

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A white-light emitting apparatus comprising: a co-fired aluminum nitride substrate; and a light emitting device arranged on a front surface of the co-fired aluminum nitride substrate,

wherein the front surface of the co-fired aluminum nitride substrate, on which the light emitting device is arranged, is mirror-polished so as to have a surface roughness of 0.3 μm Ra or less,

wherein the light emitting device comprises a vapor-deposited metal film and via holes, the vapor-deposited metal film being arranged on the front surface of the co-fired aluminum nitride substrate around the light emitting device and having a reflectivity of 90% or more with respect to light emitted from the light emitting device, and the via holes penetrating the co-fired aluminum nitride substrate from the front surface, on which the light emitting device is arranged, to the rear surface of the co-fired aluminum nitride substrate to thereby allow an electrical conduction to the light emitting device from the rear surface to the front surface without using a wire-bonding, and

wherein the vapor-deposited metal film comprises aluminum or silver and has a thickness of 1 to 5 μm , and

wherein the co-fired aluminum nitride substrate has a thickness of 0.3 to 0.6 mm.

Claim 2 (Canceled).

Claim 3 (Currently Amended): The light emitting apparatus according to claim 1, comprising a LED chip as the light emitting device and further comprising at least one peripheral component arranged on the co-fired aluminum nitride substrate, wherein the at least one peripheral component is selected from the group consisting of diodes for inhibiting reverse current, resistances, and thermistors a thermistor, a resistor, and a diode for inhibiting reverse current.

Claim 4 (Previously Presented): The light emitting apparatus according to claim 1, wherein the co-fired aluminum nitride substrate carrying the light emitting device has a surface roughness of 0.1 μm Ra or less.

Claim 5 (Previously Presented): The light emitting apparatus according to claim 1, wherein the light emitting device is mounted on the co-fired aluminum nitride substrate through a metal bump.

Claim 6 (Previously Presented): The light emitting apparatus according to claim 1, wherein a white resist film is arranged on an exposed front surface of the co-fired aluminum nitride substrate other than a region where the vapor-deposited metal film is arranged.

Claim 7 (Previously Presented): The light emitting apparatus according to claim 6, wherein the white resist film comprises a solder resist ink and is formed by screen printing method.

Claim 8 (Canceled).

Claim 9 (Previously Presented): The light emitting apparatus according to claim 1, wherein the vapor-deposited metal film is deposited via a chemical vapor deposition method or a sputtering method.

Claim 10 (Previously Presented): The light emitting apparatus according to claim 1, wherein a maximum current quantity applicable to said apparatus is 1100 to 2000 mA.

Claim 11 (Previously Presented): The light emitting apparatus according to claim 1, comprising a blue LED chip as the light emitting device and a yellow phosphor, wherein said blue LED chip is mounted on the co-fired aluminum nitride substrate and said yellow phosphor is mounted so as to cover the mounted blue LED chip.